STL57N65M5

N-channel 650 V, 0.061 Ω typ., 22.5 A MDmesh™ V Power MOSFET in a PowerFLAT™ 8x8 HV package

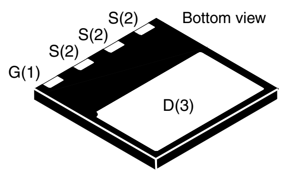
Datasheet — production data

Features

Order code	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max	I_D
STL57N65M5	710 V	0.069 Ω	22.5 A [(1)]

1. The value is rated according to $R_{thj\text{-}case}$ and limited by package

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Applications

- Switching applications

Description

This device is an N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Figure 1. Internal schematic diagram

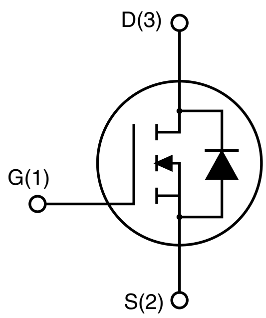


Table 1. Device summary

Order code	Marking	Package	Packaging
STL57N65M5	57N65M5	PowerFLAT™ 8x8 HV	Tape and reel

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	± 25	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	22.5	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	22	A
I_{DM} (1),(2)	Drain current (pulsed)	90	A
I_D (3)	Drain current (continuous) at T_{amb} = 25 °C	4.3	A
I_D (3)	Drain current (continuous) at T_{amb} = 100 °C	2.7	A
P_{TOT} (3)	Total dissipation at T_{amb} = 25 °C	2.8	W
P_{TOT} (1)	Total dissipation at T_C = 25 °C	189	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	9	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	960	mJ
dv/dt (4)	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	°C

1. The value is rated according to $R_{thj-case}$ and limited by package.
2. Pulse width limited by safe operating area.
3. When mounted on FR-4 board of inch², 2oz Cu.
4. I_{SD} ≤ 22.5 A, di/dt ≤ 400 A/µs, $V_{Peak} < V_{(BR)DSS}$, V_{DD}=400 V

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.66	°C/W
$R_{thj-amb}$ (1)	Thermal resistance junction-ambient max	45	°C/W

1. When mounted on FR-4 board of inch², 2oz Cu.

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	650			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 650 V V_{DS} = 650 V, T_C=125 °C			1 100	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 25 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 17.5 A		0.061	0.069	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0	-	4200 100 6	-	pF pF pF
$C_{o(er)}$ (1)	Equivalent output capacitance energy related	V_{GS} = 0, V_{DS} = 0 to 80% $V_{(BR)DSS}$	-	97	-	pF
$C_{o(tr)}$ (2)	Equivalent output capacitance time related		-	344	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	1.4	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 520 V, I_D = 17.5 A, V_{GS} = 10 V (see *Figure 15*)	-	96 24 40	-	nC nC nC

1. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
2. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$ $t_{r\,(V)}$ $t_{f(i)}$ $t_{c(off)}$	Voltage delay time Voltage rise time Current fall time Crossing time	V_{DD} = 400 V, I_D = 22.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 19*)	-	84 10.8 11 16.5	-	ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} (1) I_{SDM} (1)(2)	Source-drain current Source-drain current (pulsed)		-		22.5 90	A A
V_{SD} (3)	Forward on voltage	I_{SD} = 22.5 A, V_{GS} = 0	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 22.5 A, di/dt = 100 A/µs V_{DD} = 100 V (see *Figure 16*)	-	378 7 37		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 22.5 A, di/dt = 100 A/µs V_{DD} = 100 V, T_j = 150 °C (see *Figure 16*)	-	454 9.5 42		ns µC A

1. The value is rated according to $R_{thj\text{-}case}$ and limited by package
2. Pulse width limited by safe operating area
3. Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

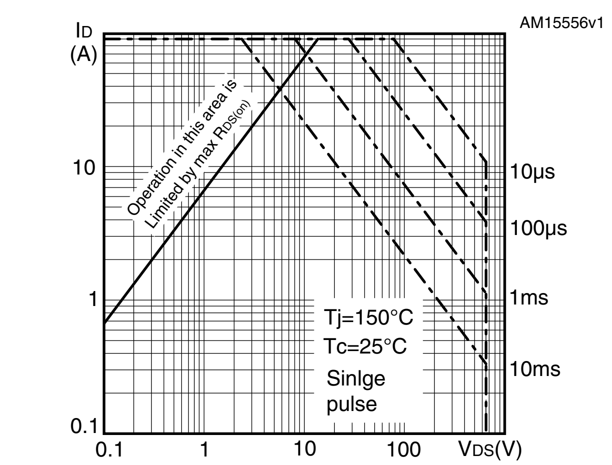


Figure 3. Thermal impedance

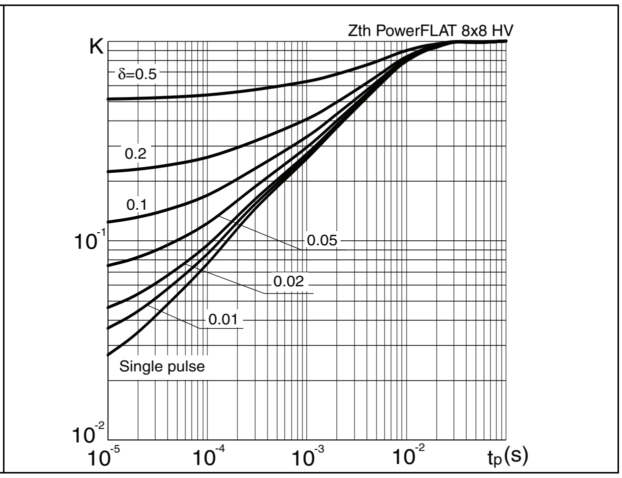


Figure 4. Output characteristics

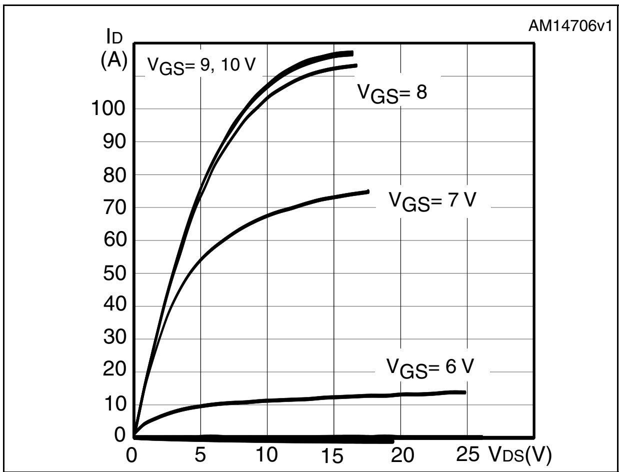


Figure 5. Transfer characteristics

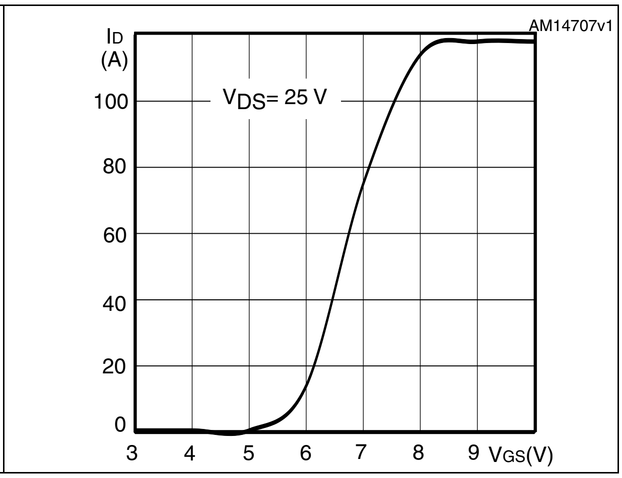


Figure 6. Gate charge vs gate-source voltage

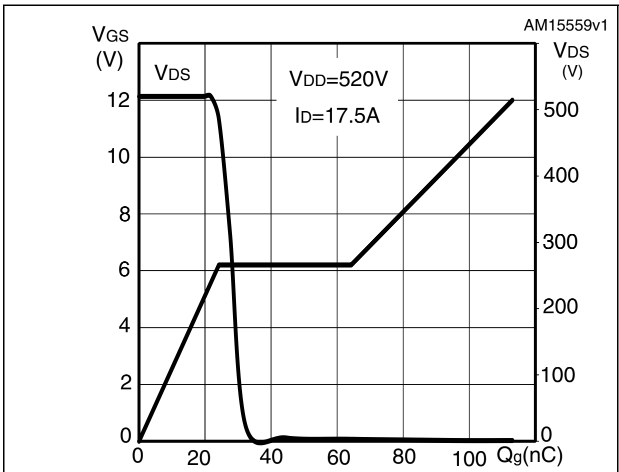


Figure 7. Static drain-source on-resistance

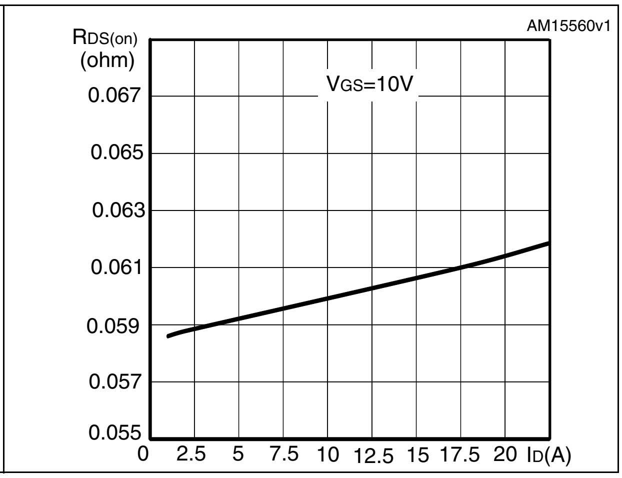


Figure 8. Capacitance variations

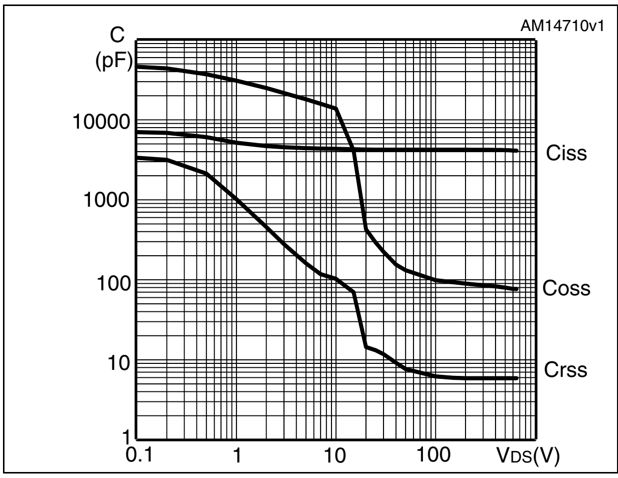


Figure 9. Output capacitance stored energy

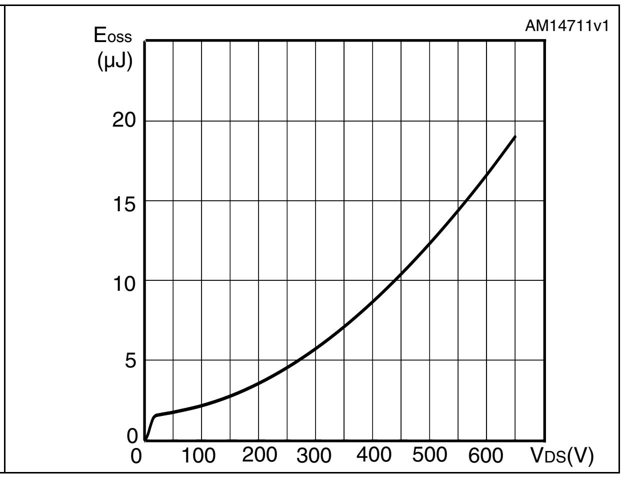


Figure 10. Normalized gate threshold voltage vs temperature

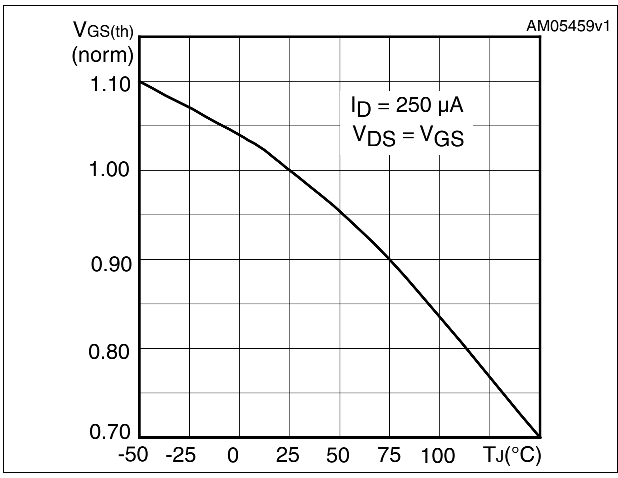


Figure 11. Normalized on-resistance vs temperature

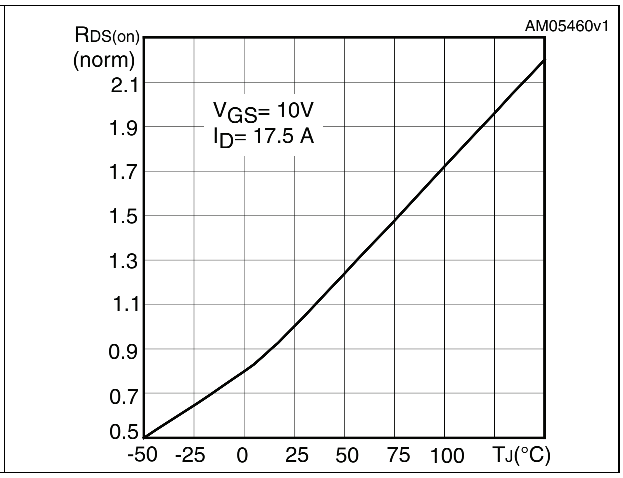


Figure 12. Normalized B_{VDSS} vs temperature

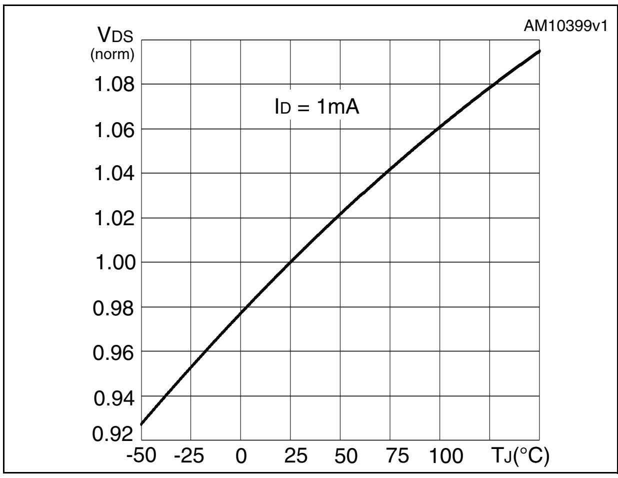
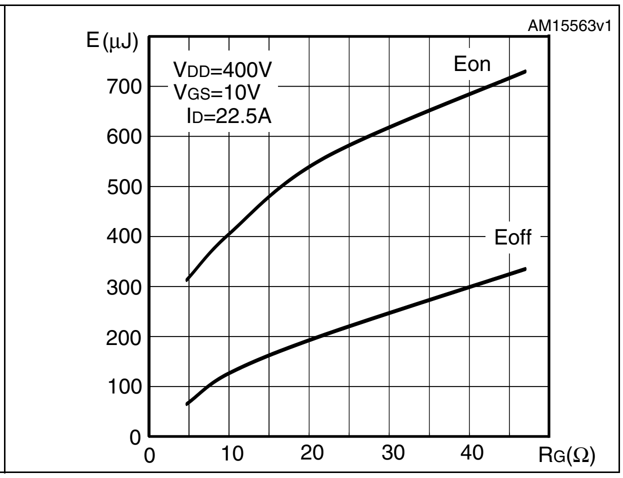


Figure 13. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode

3 Test circuits

Figure 14. Switching times test circuit for resistive load

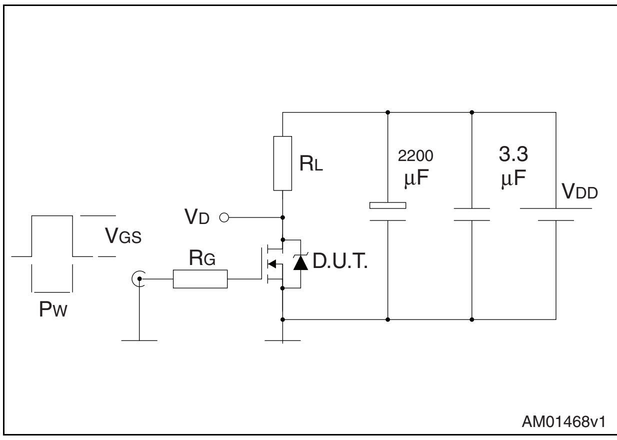


Figure 15. Gate charge test circuit

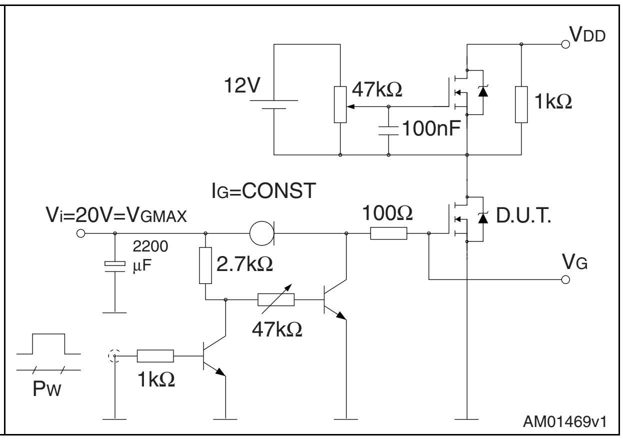


Figure 16. Test circuit for inductive load switching and diode recovery times

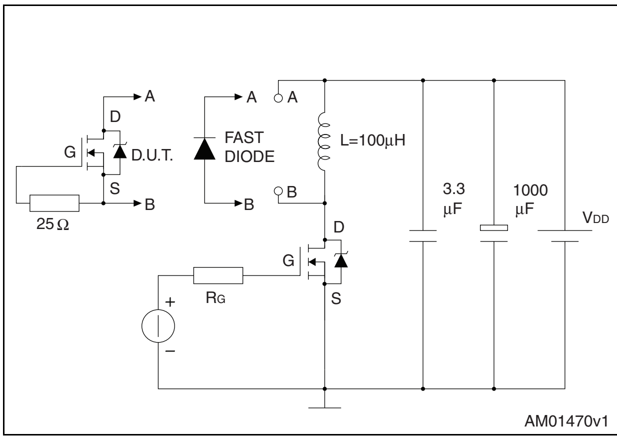


Figure 17. Unclamped inductive load test circuit

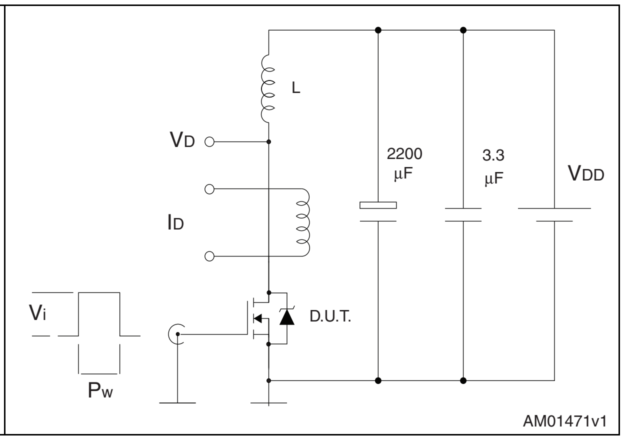


Figure 18. Unclamped inductive waveform

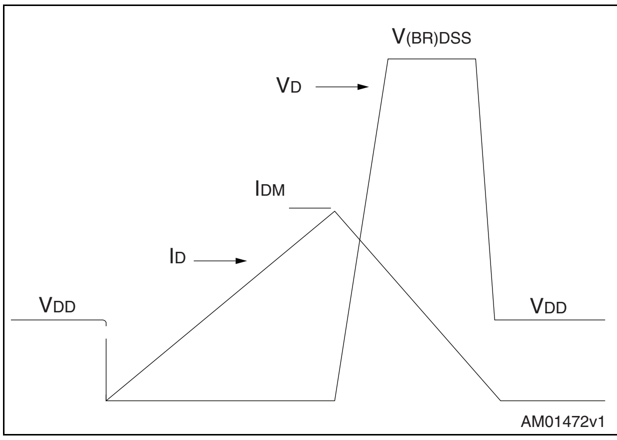
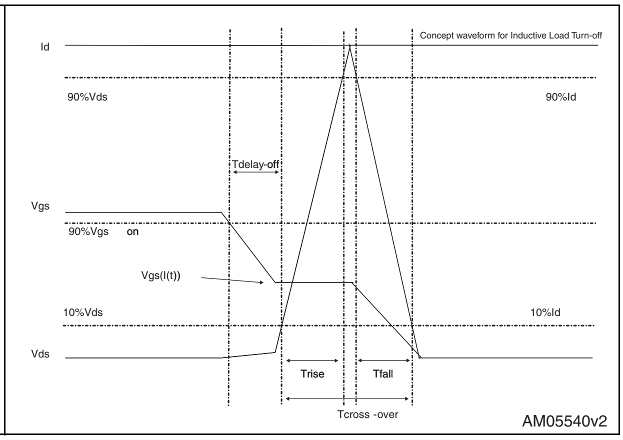


Figure 19. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

Table 8. PowerFLAT™ 8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.95	1.00	1.05
D		8.00	
E		8.00	
D2	7.05	7.20	7.30
E2	4.15	4.30	4.40
e		2.00	
L	0.40	0.50	0.60
aaa		0.10	
bbb		0.10	
ccc		0.10	

Figure 20. PowerFLAT™ 8x8 HV drawing mechanical data

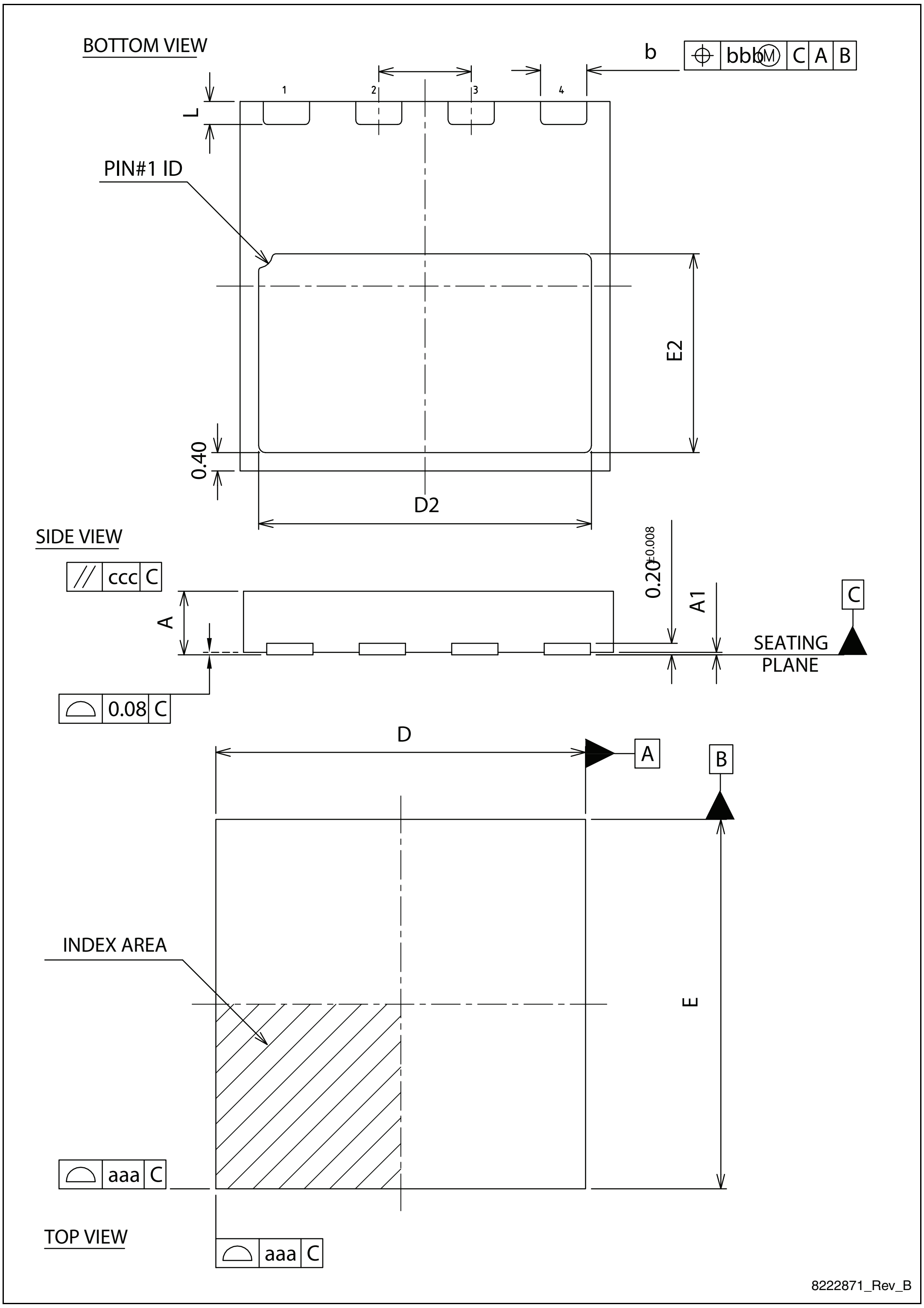
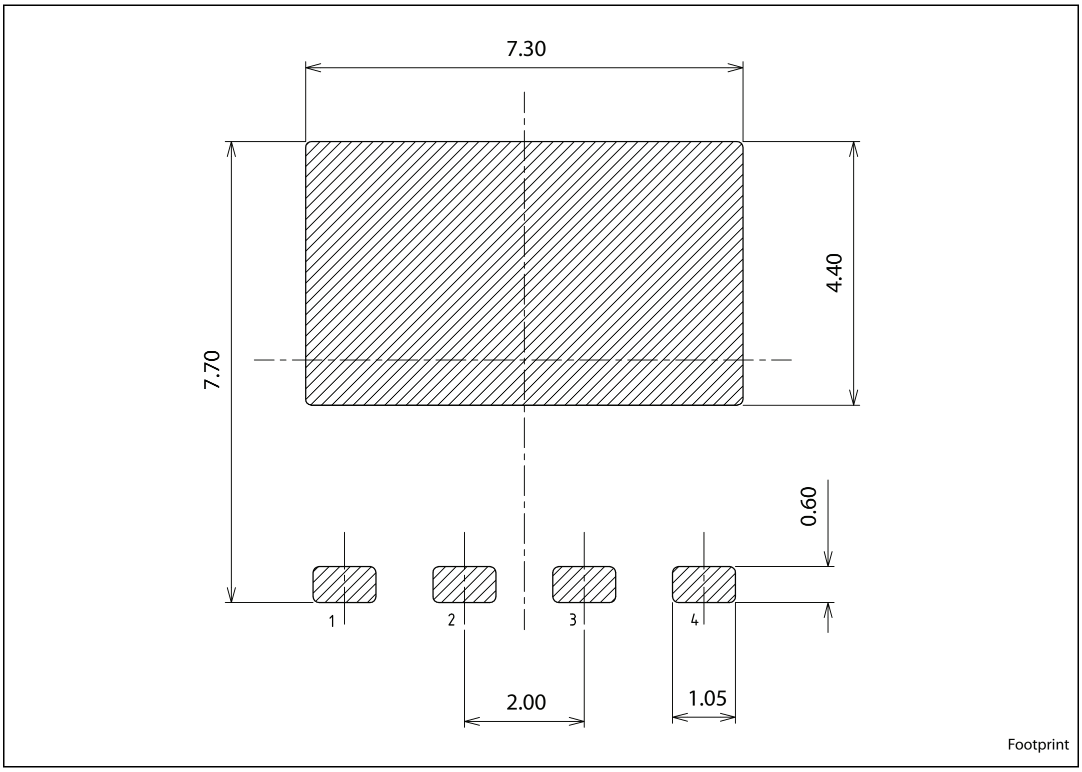


Figure 21. PowerFLAT™ 8x8 HV recommended footprint



5 Packaging mechanical data

Figure 22. PowerFLAT™ 8x8 HV tape

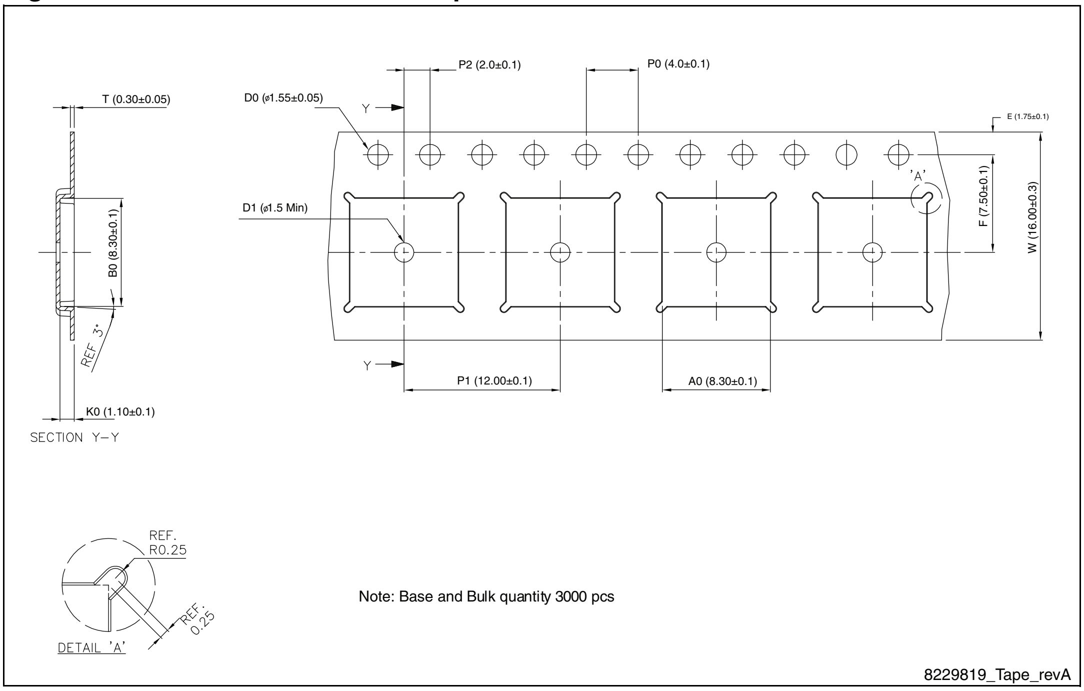


Figure 23. PowerFLAT™ 8x8 HV package orientation in carrier tape.

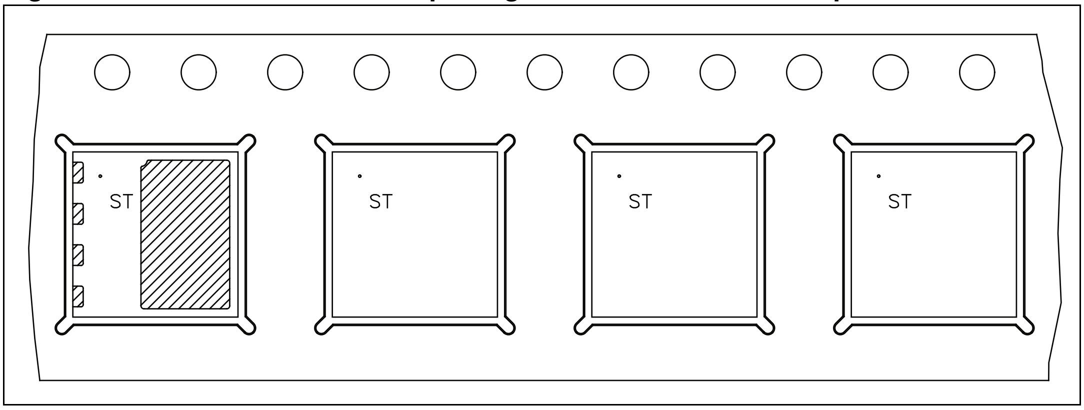
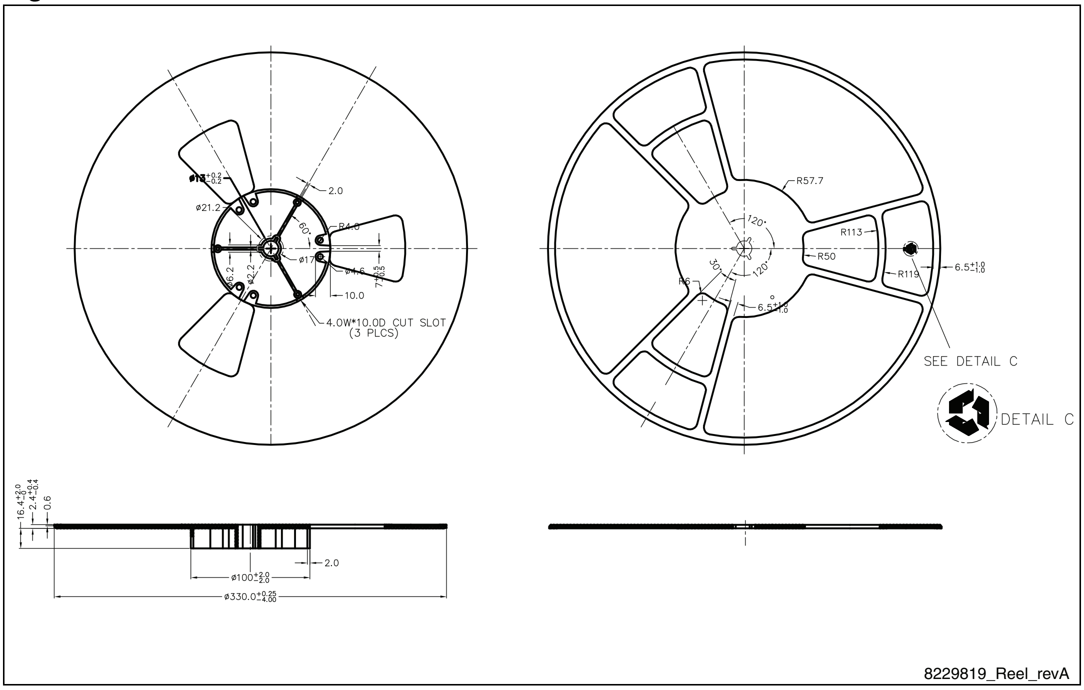


Figure 24. PowerFLAT™ 8x8 HV reel



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
14-May-2012	1	First release.
25-Jan-2013	2	– Modified: I_D value and note 1 on first page – Modified: I_D, P_{TOT}, I_{AR} values, and note 1, 4 on Table 2 – Modified: $R_{thj-case}$ value on Table 3 – Modified: $R_{DS(on)}$ on Table 4 – Modified: typical values on Table 5 and 6 – Modified: typical and max values on Table 7 – Inserted: Section 2.1: Electrical characteristics (curves) – Document staus promoted from preliminary data to production data